Gate- and magnetic field- controlled topological gap opening in the surface state of \( \text{Bi}_2\text{Se}_3 \) by proximity to a magnetic insulator

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Topological insulators are considered to be bulk insulators with exotic surface states, protected under time-reversal symmetry, which hold promise in observing many exciting condensed-matter phenomena. In this report, we show that by having a topological insulator (\( \text{Bi}_2\text{Se}_3 \)) in proximity to a magnetic insulator (EuS), a metal-to-insulator transition in the surface state, attributed to opening of an exchange gap, is observed whose properties are tunable using bottom gate voltage and external magnetic field. Our study suggests favorable band bending at the \( \text{Bi}_2\text{Se}_3/\text{EuS} \) interface leading to positioning of the Fermi level near the Dirac point. Furthermore, evidence of gate-controlled enhanced interface magnetism is observed, paving way for using magnetic proximity effect in developing topological electronic devices.

The process of breaking time reversal symmetry (TRS), by introducing out-of-plane magnetism, at the surface of a 3-dimensional (3-D) topological insulator (TI) \(^1\) is known to open up an exchange gap at the Dirac point of the topological surface states (TSS) \(^3\). Such a mechanism support several new quantum phenomena, such as quantum anomalous Hall effect (QAHE) \(^4, 5\), half-integer quantum Hall effect \(^1\) \(^6\), topological magneto-electric effect \(^7, 8\), and image magnetic monopoles \(^9\). In realizing these effects, the main challenges is to successfully demonstrate the opening of gap at the surface of TI. Currently, this is made possible in magnetic TIs such as Cr and V-doped compensated TIs, where perpendicular magnetism is developed in the bulk \(^5\) \(^10\), showing QAHE. In comparison, inducing local magnetism at the TI surface through the short range nature of magnetic proximity effect (MPE) can provide a number of advantages over bulk-doping \(^3\) \(^5\) \(^11\): these include lower bulk and surface defect density due to improved film crystallinity, better controllability of the surface states (SS) from the bulk and the ability to independently control the magnetic state at each surface of TI. 

Conventionally, MPE can be achieved by using magnetic insulators (MIs). However, the requirement of an out-of-plane magnetization at the TI surface makes this study difficult since most of the MIs naturally possess in-plane anisotropy. Additionally, new hybridization states \(^12\) form at the TI/MI interface near the Fermi level (\(E_F\)) that can contaminate the topological properties of the Dirac SSs \(^13, 14\). As a result, observing these effects through transport studies can become non-trivial. In this regard, MPE studies in the 3D TI, Bismuth Selenide (\( \text{Bi}_2\text{Se}_3 \)), with an MI, Europium sulphide (EuS), have been extensively researched using magnetometry techniques \(^15\) \(^16\). Different research groups confirm the presence of an out-of-plane component of magnetization at the \( \text{Bi}_2\text{Se}_3/\text{EuS} \) interface with the magnetism existing at temperature much above the magnetic transition temperature \((T_m)\) of EuS \((\sim 17 \text{K})\). Unlike other TI/MI interfaces \(^13\) \(^14\) \(^17\) \(^18\), recent theoretical calculation of the above interface have also suggested induced magnetism \(^21\), localized within the first quintuple layer (QL) of \( \text{Bi}_2\text{Se}_3 \), with the SS retaining most of the topological character compared to a pristine \( \text{Bi}_2\text{Se}_3 \) SS \(^22\). Further, an induced exchange gap of \(\sim 9 \text{ meV} \) in the surface Dirac cone is suggested \(^21\).

Despite these reports, experimental observation of the exchange gap opening at this surface has been elusive \(^23\). This is primarily due to inherent intrinsic doping caused by large Se vacancies leading to bulk dominated conduction with \(E_F\) pinning deep inside the conduction band (CB). In this letter, we provide evidence for favorable band bending at the \( \text{Bi}_2\text{Se}_3/\text{EuS} \) interface leading to \(E_F\) dropping below the CB, thereby gaining access to the SSs in our transport measurements. Under these conditions, a gate and magnetic-field controlled metal-to-insulator transition (MIT) is observed in these SSs which we attribute to the opening of exchange gap.

High quality thin films of \( \text{Bi}_2\text{Se}_3 \) were grown on Si(100)/SiO\(_2\) (300 nm) substrate at 250°C in our molecular beam epitaxy system with a base pressure of \(8 \times 10^{-10} \text{mbar}\) using co-evaporation of Bi and Se with a flux ratio (Bi:Se) varied between 1:15 to 1:20. The structural properties of the films were studied using Raman spectroscopy, X-ray diffraction and Transmission electron microscopy (TEM) (see Fig. S1 in Supp. Mater.). Interestingly, cross-sectional TEM images reveal a layered growth, supporting the hexagonal structure with 0.95 nm thickness of the QL (inset of Fig. 1). For the case of transport measurements, thicker \( \text{Bi}_2\text{Se}_3 \) films in \(\sim 10\) to 16 nm range were grown. Subsequently, a 3 nm film of EuS was deposited in a sulphur-rich environment at room temperature, without breaking vacuum, followed by a 2 nm-capping layer of Al\(_2\)O\(_3\). Hall bar structures (with length, \(L\) and width, \(W\)) were patterned by mechanical etching. Figure 1a shows the temperature dependence of the longitudinal resistivity \((\rho_{xx})\) of \( \text{Bi}_2\text{Se}_3 \) films for three
different capping layers viz. 2 nm Al₂O₃, 2 nm Se and 3 nm EuS. Films with Al₂O₃ capping layer show predominantly a metallic signature with a weak upturn in film resistivity at ~28K followed by a metallic signature at lower temperatures. This marginal increase in resistivity may be arising due to freezing out of thermally activated conductivity of the impurity bands. In comparison, the Bi₂Se₃ films with Se and EuS capping layers show an upward trend in resistivity below 20K, with a stronger response in the latter. For all the devices, the bulk Hall carrier density \( N_B \) was extracted to be \( \sim 10^{19} \text{ cm}^{-3} \) at 1.5K which often leads to \( E_F \) pinning near the CB minimum. Also, the Hall mobility of the devices were found to be \( \sim 450 \text{ cm}^2/\text{V} \cdot \text{s} \), which is an order of magnitude higher than the critical mobility \( \mu_{IR} \sim 20 \text{ cm}^2/\text{V} \cdot \text{s} \) for our devices; see section 2 in Suppl. Mater.) determined by the Ioffe-Regel mechanism for the onset of disorder driven variable range hopping transport. Therefore, the above observation and the fact that our film mobility increases with cool down (see Fig. S3) rule out bulk disorder as the source for the strong upturn in the film resistivity below 20K.

The observation of an increase in resistivity in the Se and EuS capped devices compared to a drop in the Al₂O₃ capped devices rather hint to the strong role of top surface modifications, possibly mediated by the band bending effects (refer to section 3 in Supp. Mater.). The relatively lower mobility of our films on Si/SiO₂ substrates compared to epitaxial films (1000 \( \text{cm}^2/\text{V} \cdot \text{s} \)) may have an advantage of detecting a larger contribution of SS to the overall device resistance. At the surface of a TI, the position of the \( E_F \) is greatly dependent on the relative concentration of bulk and surface defect density. A large mismatch in the surface and bulk \( E_F \) leads to charge transfer and bending of bulk bands. The observation of a metallic response in the Al₂O₃ capped devices support the formation of a downward band bending at the Bi₂Se₃/Al₂O₃ interface as shown in the left inset of figure 1. In order to investigate the insulating behaviour of the other two devices, i.e. Bi₂Se₃/Se (control device) and Bi₂Se₃/EuS (bilayer device), temperature dependence of Hall carrier density \( n_{Hall} \) is plotted in Fig 1b. Capping the Bi₂Se₃ film by Se can significantly reduce the surface defect density compared to the bulk, causing the \( E_F \) at the surface to lower below the CB. Such an upward band bending process leads to a sudden drop in Hall carrier density below 20K, seen in figure 1d, and a resultant marginal increase in device resistance as noted in figure 1b, below ~20K. Similar behaviour is also noted in our bilayer devices which is a very intriguing result because, in literature, interface potential mismatch between stoichiometric Bi₂Se₃ and EuS suggests a downward band bending with the formation of a metallic non-topological quantum well states. Our experimental signature of an upward band bending therefore highlight that relative difference in the surface to bulk defect density in the Bi₂Se₃ films is playing a more dominant role over the interface work function mismatch in pinning the interface \( E_F \). Density functional theory (DFT) studies have shown that Eu-Se bond formation at the Bi₂Se₃/EuS interface is more favorable. This may cause lower surface defect density supporting an upward band bending, similar to the control devices.
Although the Se and EuS capped films show similar upturn in film resistivity, the cool down response of the EuS capped devices showed distinct dissimilarities from our control devices. Firstly, the drop in resistivity from 100K is found to be gradual compared to the other two devices, a trend observed in different samples with different W (200 μm to 2 mm). In addition, a strong gate voltage and field-cooled modifications to the insulating transition was noted in the Bi₂Se₃/EuS devices (Fig 2 and Fig 3), not observed in the latter (refer to Fig. S5). To investigate the effect of upward band bending on the topological properties of the Bi₂Se₃ SS, weak antilocalization (WAL) studies using magneto-conductance \( G(B) \) measurements were performed at low temperatures (< 30K). A sharp upward cusp in \( G(B) \) at zero magnetic field, attributed to suppressed backscattering in the topologically protected SS, was observed in both the bilayer and the control devices. Figure 1 shows \( \Delta G(B) \) vs B for the two devices measured at 1.5K, showing a smaller effect in the bilayer devices compared to our control devices. The magneto-conductance data for the two Hall bar devices with L/W ~1 was fitted to the Hikami-Larkin-Nagaoka (HLN) formalism given by \( \Delta G(B) = \frac{4e^2}{\pi h} \ln\left(\frac{B_\phi}{B}\right) - \frac{\psi(1/2 + B_\phi/B)}{\sqrt{1+B_\phi}} \), where \( \psi(x) \) is the digamma function [32], e is charge and \( h \) is Planck’s constant. The temperature dependence of the fitting parameters, dephasing field \( B_\phi \) and prefactor, \( \tilde{A} \), that denotes the effective number of 2D conducting channels contributing to WAL is plotted in figure 1. A drop in \( \tilde{A} \) from a value of 2 (bottom and top 2D surface channels) in the control devices (showing a value of 1.6 in our devices), approaching 1 at higher temperatures, is expected due to the parallel bulk conduction that couples the top and bottom surface 2D channels of the Bi₂Se₃ film [33]. Interestingly, at 1.5K when the bulk conduction is reduced, although both the devices show similar value of \( B_\phi \), a considerable drop in \( \tilde{A} \) by a value of 0.8 (~1 channel) is observed in the bilayer devices. These reports may be explained (below) by the MPE opening up a gap at the top surface, leading to only the bottom surface channel contributing to WAL.

Figure 2 shows the effect of back gate voltage \( V_g \) to the insulating transition observed in the Bi₂Se₃/EuS devices. Here, the high bulk carrier density and a weak back gating prevents the movement of bulk \( E_F \) towards the Dirac point, thereby only modulating the band bending near the surface. At negative \( V_g \), the insulating transition was observed at temperature, \( T_{MIT} \sim 19K \), which is enhanced to ~32K at positive \( V_g \) (top inset of Fig 2). This marked difference in the gate-controlled response, compared to no change in our control devices, suggest the presence of an additional effect that is driving the transition apart from the upward band bending at the top Bi₂Se₃/EuS interface. The strong spin-orbit interaction at the Bi₂Se₃ surface is shown to prefer out-of-plane magnetic anisotropy of EuS layer in the interface region, observable even close to room temperature [17]. This out-of-plane magnetization can open up an exchange gap in the SS of Bi₂Se₃ contributing to an activated transport when the \( E_F \) is close to the Dirac point leading to MIT. Our magnetometry studies on Bi₂Se₃(10nm)/EuS(1nm) also confirm the existence of enhanced interface magnetism with a second transition close to 32K (Fig. S4). However, at higher temperatures (> \( T_{MIT} \)), the interface magnetism may be quite weak to open up a sizeable exchange gap in our devices. Also, upward band bending effect will be weaker with the \( E_F \) away from the Dirac point. Below \( T_{MIT} \) when the EuS layer becomes magnetic, interface magnetism gets stronger and the MPE leads to opening of an observable exchange gap.

The increase in \( T_{MIT} \) at positive \( V_g \), which also makes the device conducting (seem by the downward shift of the plots in figure 2), at first seems counter-intuitive. However, raising the \( E_F \) in the bilayer film leads to an increase in carrier density at the Bi₂Se₃/EuS interface (top inset of Fig 2). Such an observation is suggestive of conduction-electron-mediated ferromagnetic exchange between the Eu atoms strengthening the interface magnetism, with an enhancement in \( T_c \) of the EuS interface layer. Existence of such a mechanism was theoretically predicted in a recent work by Kim et. al. [22]. This enhanced interface magnetism can open up a larger exchange gap which may be responsible for the larger increase in resistance under positive \( V_g \), peaking at \( V_g \sim 50V \) (bottom-right inset of Fig 2).
FIG. 3. $R_{xx}$ vs $T$ of the Bi$_2$Se$_3$(16 nm)/EuS(3 nm) device measured at $V_g = 50$V with varying perpendicular $H_{FC}$. The plots are shifted vertically for clarity. Bottom right inset shows lowering of $T_{MIT}$ with $H_{FC}$ attributed to the weakening of the indirect exchange at the interface.

even at high negative $V_g$ (depleted interface) which may indicate the role of high spin-orbit strength leading to an enhancement in the Tc of the bulk EuS film. However, this difference can also arise due to the initial resistance increase caused by the lowering of interface $E_F$, below the CB minimum. At positive $V_g$ (> 30V), the resistance plots show a point of inflection at 19K, below which, the resistance increases further. This feature may therefore correspond to the magnetic transition of EuS layers away from the interface at 19K, unaffected by the above indirect exchange interactions.

In EuS, magnetism arises due to the overlap of the Eu 4f orbitals with the valence band below the $E_F$ leading to a weaker exchange coupling [34]. DFT studies by Kim et. al. [22] have shown that the TSSs that weakly interconnect the conduction and valance bands can mediate exchange coupling between Eu atoms through the Ruderman-Kittel-Kasuya-Yosida (RKKY) [35–37] type interactions, with the exchange constant being sensitive to the position of $E_F$ near the Dirac point. The observed gate controlled tuning of $T_{MIT}$ in our devices does provide evidence for the existence of such an indirect exchange mechanism at the Bi$_2$Se$_3$/EuS interface. To further investigate these interactions, the devices were cooled down in different perpendicular magnetic fields ($H_{FC}$), keeping $V_g$ at 50V, as shown in figure [3]. Firstly, we observe a decrease in $T_{MIT}$ with the increasing strength of $H_{FC}$ (inset of Fig [3]). This may be suggestive of the weakening of the antiferromagnetic exchange between the conduction electrons and the Eu 4f atoms observed in such indirect exchange interactions. Additionally, at zero or low magnetic fields (also seen in Fig[2] for positive $V_g$ values), a very prominent and reproducible drop (observed in different devices) in the device resistance precedes the MIT. This sudden drop in resistance, by almost 10 Ω (for data at $H_{FC} = 0$), may be suggestive of formation of 1D chiral fermion edge states [1] along the magnetic domain walls at the interface around $T_c$, with the simultaneous opening of the exchange gap. With the lowering of temperature, domains become larger leading to a dominant insulating transport response due to the exchange gap opening. Notably, when cooled in higher magnetic fields, the domain with parallel magnetization grows at the onset of magnetism, resulting in the reduction of domain wall that support these conducting edge channels. As a result, the resistance drop becomes invisible at large $H_{FC}$. These observations of the dip in resistance before MIT, which we attribute to the formation of conducting channels at the domain walls, also highlight that the interface-gapped states in our devices do carry topological properties, and the MIT response of our devices is not due to the formation of any trivial hybridization gap [15]. These topologically non-trivial gapped states should therefore provide evidence of half-integer-quantized Hall conductivity by tuning the $E_F$ in the exchange gap.

In an effort to probe the quantized Hall conductivity, variation in $R_{xx}$ and Hall resistance ($R_{xy}$) of the bilayer device with $V_g$ was measured (see Fig [4]). Firstly, a hysteresis response in $R_{xx}$ is observed at all temperatures below 125K, with similar temperature response observed in 4 different sets of samples. In comparison, the control devices showed no such behavior. Our analysis suggest
that the hysteresis in $R_{xx}$ arise due to weaker gating, with the interface $E_F$ pinning/de-pinning within the band gap of Bi$_2$Se$_3$. The fact that the onset of hysteresis occurs around the same temperature when the carrier density falls down ($T < 100K$) corroborates well with the mechanism related to band bending and the $E_F$ at the interface dropping into the band gap. In figure 4, a second smaller hysteresis response is noted, extending to positive gate voltage, observed in different samples with varying Hall bar width and film thickness (refer to Fig. S6). We attribute the origin of the second hysteresis to the opening of the exchange gap and the associated $E_F$ pinning/de-pinning within this exchange gap. $R_{xy}$ also showed a hysteresis response with a resistance plateau (see Fig. 4) of $\sim 70$ mΩ for $V_g > -27$V (in the negative sweep cycle of $V_g$, peaking to 85mΩ at $V_g = -23$V) which we associate to the condition of $E_F$ lying in the exchange gap of the SSs. Furthermore, the hysteresis and the step increase in $R_{xy}$ disappear in presence of small magnetic field (> 100 Oe), without an appreciable change in the hysteresis response of $R_{xx}$. These observations further validate the origin of resistance plateau in $R_{xy}$ to the existence of domain walls that support chiral edge states. Here, the existence of bulk conduction and bottom Dirac SS are limiting the observation of half-integer value of quantized Hall conductance.

We would also like to mention that unlike previous studies showing induced magnetism in the Bi$_2$Se$_3$ films through weak anomalous Hall effect (AHE) [10], our investigations do not show any such signature at lowest measurable temperature of 1.4K, confirming the localized nature of the magnetism in the interface EuS layer responsible for the opening of the exchange gap. Further, formation of a third Dirac state, as reported in DFT studies [21, 22], is not observed from our HLN analysis. It could be that these states do not exist around the $E_F$ in our devices. In conclusion, our present work highlights the richness of the Bi$_2$Se$_3$/EuS interface with the possibility of using MPE to open up an exchange gap in the surface state of TI. Furthermore, we also demonstrate preserving the topological properties of the exchange gap by reporting signatures of chiral edge states and the corresponding Hall resistance that vanishes in presence of magnetic field. Reducing bulk conduction to observe half-integer quantized Hall resistance remains a challenge for future studies. These measurements will possibly bring us one step closer in realizing QAHE in an MI/TI/MI device structure [38].

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I. STRUCTURAL CHARACTERIZATION OF Bi$_2$Se$_3$ FILMS

Thin films of Bi$_2$Se$_3$ in the range 6 nm to 16 nm were grown on Si/SiO$_2$ (300 nm) and c-cut sapphire substrates. 3 nm EuS films were grown on Bi$_2$Se$_3$ layer at different substrate temperatures viz. room temperature, 100°C and 200°C. X-ray diffraction (XRD) studies were performed to determine the film thickness and the crystallographic information. In the case of sapphire substrate, epitaxial growth of the Bi$_2$Se$_3$ films was noted from the observation of sharp (003) and (006) peaks supporting the hexagonal structure of the films (Fig. S5a).

High temperature grown EuS films were observed to weaken the crystallinity of the underneath Bi$_2$Se$_3$ films, as noted from the reduced intensity of the (006) peak. Hence, for most of the devices measured in this work, room temperature grown EuS films were preferred. In the case of Si/SiO$_2$ substrate, XRD 2-theta scan reveal a predominant layered hexagonal structure of the Bi$_2$Se$_3$ films (with sharp crystallographic peaks) with a weak presence of orthorhombic phase (Fig. S5b). Furthermore, our Raman measurements (Fig. S5c) confirm the three dominant peaks of the rhombohedral phase at 72 cm$^{-1}$, 131 cm$^{-1}$ and 174 cm$^{-1}$, consistent with the $A_{1g}$, $E_2^g$ and $A_{2g}$ observed in the previous studies [S1,S2]. The out-of-plane mode $A_{1g}$ is in-phase vibrations, while the in-plane mode $E_2^g$ and the out-of-plane mode $A_{2g}$ are out-of-phase vibrations. In-plane $E_1^g$ mode was not clearly observed in our measurement due to the detector limitation. Again, similar to our results on epitaxial films, the room temperature grown EuS samples showed marginally better Raman signals (sharper $A_{1g}$ peak) of the Bi$_2$Se$_3$ films on SiO$_2$ substrate.
II. CALCULATION OF HALL CARRIER DENSITY AND HALL MOBILITY

FIG. 6. Presence of two surface states in a TI film contribute to the overall Hall resistance $R_{xy}$, measured using the device configuration shown in the right. Here, $t$ is the film thickness, $B_z$ is the normal magnetic field, $I$ is the current and $R_{xx}$ is the longitudinal resistance.

The Hall measurements of a topological insulator requires careful analysis due to the presence of modest carrier densities at the Dirac surface states which are not present in the bulk. Bulk Hall carrier concentration, $N_B$ (in units of cm$^{-3}$), in a medium is determined using the equation $R_{xy} = (1/(N_B \cdot q \cdot t))B_z$. However, such a calculation can introduce sufficient error in TIs if the Fermi level at the surface is away from the Dirac point. In such a scenario, the Hall carrier density (in units of cm$^{-2}$) may be given by $n_{Hall} = n_{top}^{SS} + n_{bottom}^{SS} + t \cdot N_B$. Assuming the linear Dirac dispersion of the surface of Bi$_2$Se$_3$ with Fermi velocity of $4.0 \times 10^5$ m/s, and the Fermi level at the surface positioned at the conduction band minimum (flat band condition) i.e. $\sim 210$ meV above the Dirac point, the carrier density associated to each spin-momentum locked surface of the Bi$_2$Se$_3$ film would be $n_{top}^{SS} = n_{bottom}^{SS} \sim 5 \times 10^{12}$ cm$^{-2}$ [25]. For our films, $n_{Hall}$ is determined to be $\sim 3 \times 10^{13}$ cm$^{-2}$ suggesting a sizeable contribution (20-25%) of the surface carriers compared to the bulk carriers to the Hall voltage. This contribution from the surface carriers is expected to come down if the Fermi level at the surface drops below the conduction band edge, which can happen due to band bending effects. For our film thickness, $t \sim 12$ nm, a lower limit on $N_B$ is determined to be around $\sim 2 \times 10^{19}$ cm$^{-3}$.

FIG. 7. Hall mobility vs T for the control and bilayer devices for 12 nm thickness of Bi$_2$Se$_3$ films

The Hall mobility of the devices were calculated to be $\sim 450$ cm$^2$/V·s. Temperature dependence of the Hall mobility is shown in Figure S3, showing band transport feature with the mobility increasing with cool down. The critical mobility ($\mu_{IR}^{CR}$) determined by the Ioffe-Regel mechanism [25] is given by: $\mu_{IR}^{CR} = (2\pi e / \hbar)(3\pi^2 n_{Hall}/t)^{-2/3}$, where $t$ is the film thickness, $e$ is charge and $\hbar$ is Planck’s constant [25]. Using $n_{Hall} \sim 3 \times 10^{13}$ cm$^{-2}$ and $t \sim 12$ nm for our devices, $\mu_{IR}^{CR}$ is calculated to be 20 cm$^2$/V·s, which is an order of magnitude lower than the Hall mobility of our films.

III. BAND BENDING EFFECTS

Typically, band bending across an interface happen due to mismatch in the Fermi level leading to charge transfer across the interface. However, in a TI, the presence of additional Dirac surface states leads to process of charge transfer to equilibrate the surface and bulk Fermi levels leading to band bending at the TI surface. It is important to note that the calculation of bulk carrier density from the Hall measurement only provides an average value without
much information of density variation with depth. Capping of the top surface of the TI with Se, can significantly reduce the defect density at the surface compared to the bulk of film. Theoretically, flat-band condition is attained when the surface defect density is $\sim 5 \times 10^{-12} \text{ cm}^{-2}$ (value determined from section II). For surface defect density more than $\sim 5 \times 10^{-12} \text{ cm}^{-2}$, charge transfer happens from the surface to the bulk [25]. As a result, Fermi level raises above the conduction band minima, leading to metallic signature. Similar mechanism may be happening in the case of Bi$_2$Se$_3$/Al$_2$O$_3$ devices (Figure 1a). However, when the surface defect density reduces below $\sim 5 \times 10^{-12} \text{ cm}^{-2}$, charge transfer from bulk to the surface support upward band-bending which leads to lowering of the surface Fermi level into the surface states, indicating an increase in resistance as observed in the Bi$_2$Se$_3$/Se and Bi$_2$Se$_3$/EuS devices.

In case of upward band bending, a depletion width ($z_D$) may be estimated using an abrupt junction model by solving the Poisson’s equations giving [25]:

$$z_D = \left(\frac{2\epsilon_0\epsilon_r \cdot \Delta V}{e^2 N_B}\right)^{1/2},$$

where $\epsilon_r$ is the dielectric constant ($\sim 113$ for Bi$_2$Se$_3$), $\Delta V$ is the magnitude of conduction band bending and $N_B$ is the bulk defect density. Taking a typical estimate of $N_B \approx 4 \times 10^{19} \text{ cm}^{-3}$ in a typical thicker Bi$_2$Se$_3$ films, and $\Delta V \approx 210 \text{ meV}$ (i.e. Fermi level close to the Dirac point at the surface) leads to $z_D$ of $\sim 8 \text{ nm}$. This value seems reasonable compared to our film dimensions where we observe these effects.

IV. MAGNETOMETRY MEASUREMENTS

In order to investigate the presence of enhanced magnetism at the Bi$_2$Se$_3$/EuS interface, a sample of Bi$_2$Se$_3$ (10 nm)/EuS(1 nm) films were grown for characterization using SQUID (see Figure S8). Magnetization ($M$) vs $T$ measurements and susceptibility analysis suggest the presence of magnetic transition at 232K and another one at 16K which may correspond to the bulk $T_C$ of EuS. A $T_C$ of 16K for 1 nm EuS is significantly higher than the $T_C$ observed in SiO$_2$/EuS (1 nm) films suggesting role of the stronger spin-orbit interaction of the surface of Bi$_2$Se$_3$ in the above enhancement. The observation of a magnetic transition at temperature close to 232K does confirm previous reports [17] of close to room temperature interface magnetism observed in such bilayer systems.

![Graph](image)

**FIG. 8.** (a) SQUID magnetometry measurement of $M$ using zero-field cooled (ZFC) conditions at 100 Oe and (b) susceptibility calculated from (a) of EuS/ Bi$_2$Se$_3$ bilayer film.

V. GATE- AND MAGNETIC FIELD- CONTROLLED RESPONSE OF BI$_2$SE$_3$/SE CONTROL DEVICE

Figure S9a shows the longitudinal resistance, $R_{xx}$, of the control device vs $T$, measured at different gate voltages ($V_g$), ranging from -60 to +60V. The devices showed no observable dependence on $V_g$ at low temperatures. Additionally, $R_{xx}$ vs $V_g$ was measured at different temperatures. Unlike our bilayer devices, these samples showed no sign of hysteresis. The devices were also cooled down in magnetic field showing no dependence on the insulating transition, apart from the weak-anti localization (WAL) effects that marginally increases the resistance of the device in field at low temperatures.
VI. GATE CONTROLLED HYSTERESIS RESPONSE OF Bi$_2$Se$_3$/EuS DEVICE

Gate controlled hysteresis response as shown in figure 4 and figure S10 was observed in different samples with the thickness of Bi$_2$Se$_3$ films varied between 10 nm to 16 nm. Figure S10 shows the zoom-in-view of the $R_{xx}$ vs $V_g$ data of figure 4 below 25K. Similar experiments, as shown in figure 4, were performed in devices with reduced $W=200$ µm (deposited using shadow mask) in Bi$_2$Se$_3$(12nm)/EuS(3nm) devices.

Figure S10 shows the hysteresis response observed in the above device for $T>20$K, showing similar behavior to the devices of figure 4. Variation in the gate voltage range where the hysteresis is observed is noted between different samples. Compared to figure 4, the hysteresis response is shifted towards positive gate voltage. This may be attributed to variation in the position of the Fermi level and the associated band bending at the Bi$_2$Se$_3$/EuS interface between different devices with varying film thickness. In these resistive samples (due to the narrower width) below 20K, a much bigger (merged) hysteresis response is observed extending to even large negative gate voltages. This is shown in Figure S10.

VII. REFERENCES